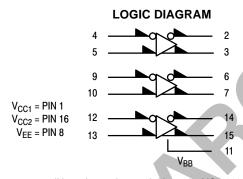
High Speed Triple Line Receiver

The MC10216 is a high speed triple differential amplifier designed for use in sensing differential signals over long lines. The base bias supply (V_{BB}) is made available at pin 11 to make the device useful as a Schmitt trigger, or in other applications where a stable reference voltage is necessary.

Active current sources provide the MC10216 with excellent common mode noise rejection. If any amplifier in a package is not used, one input of that amplifier must be connected to V_{BB} (pin 11) to prevent upsetting the current source bias network.

Complementary outputs are provided to allow driving twisted pair lines, to enable cascading of several amplifiers in a chain, or simply to provide complement outputs of the input logic function.

- $P_D = 100 \text{ mW typ/pkg (No Load)}$
- $t_{pd} = 1.8$ ns typ (Single ended)
- = 1.5 ns typ (Differential)
- t_r , $t_f = 1.5$ ns typ (20%–80%)



 $^*V_{BB}$ to be used to supply bias to the MC10216 only and bypassed (when used) with 0.01 μF to 0.1 μF capacitor.

When the input pin with bubble goes positive, it's respective output pin with bubble goes positive.

DIP PIN ASSIGNMENT



Pin assignment is for Dual–in–Line Package.
For PLCC pin assignment, see the Pin Conversion Tables on page 18 of the ON Semiconductor MECL Data Book (DL122/D).



ON Semiconductor

http://onsemi.com

MARKING DIAGRAMS



CDIP-16 L SUFFIX CASE 620





PDIP-16 P SUFFIX CASE 648





PLCC-20 FN SUFFIX CASE 775



A = Assembly Location

WL = Wafer Lot YY = Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC10216L	CDIP-16	25 Units / Rail
MC10216P	PDIP-16	25 Units / Rail
MC10216FN	PLCC-20	46 Units / Rail

ELECTRICAL CHARACTERISTICS

Characteristic Power Supply Drain Current Input Current Output Voltage Logic	Symbol t I _E I _{inH} I _{CBO}	Pin Under Test 8	Min	0°C Max	Min	+25°C	•	+85	o~C	1
Power Supply Drain Current Input Current	t I _E	8	Min	Max	Min	I Tvn	l			
Input Current	I _{inH}					†	Max	Min	Max	Ų
		4		27		20	25		27	m
Output Voltage Lesia	I_{CBO}	1		180			115		115	μ
Output Voltage Lasia		4 9		1.5 1.5			1.0 1.0		1.0 1.0	μ
	1 V _{OH}	2	-1.060	-0.890	-0.960		-0.810	-0.890	-0.700	١
Output voltage Logic	VOH	3	-1.060	-0.890	-0.960		-0.810	-0.890	-0.700	`
Output Voltage Logic	0 V _{OL}	2	-1.890	-1.675	-1.850		-1.650	-1.825	-1.615	١
		3	-1.890	-1.675	-1.850		-1.650	-1.825	-1.615	4
Threshold Voltage Logic	1 V _{OHA}	2	-1.080 -1.080		-0.980 -0.980			-0.910 -0.910		1
Threshold Voltage Logic	0 V _{OLA}	2	1.000	-1.655	0.500		-1.630	0.510	-1.595	7
Threshold voltage Logic	VOLA	3		-1.655			-1.630		-1.595	`
Reference Voltage	V_{BB}	11	-1.420	-1.280	-1.350		-1.230	-1.295	- 1.150	١
Switching Times (50Ω Load	d)								•	
Propagation Delay	t ₄₊₂₊	2	1.0	2.6	1.0	1.8*	2.5	1.0	2.8	
	t ₄₋₂₋	2	1.0	2.6	1.0	1.8*	2.5	1.0	2.8	
	t ₄₊₃₋ t ₄₋₃₊	3	1.0 1.0	2.6 2.6	1.0 1.0	1.8* 1.8*	2.5 2.5	1.0 1.0	2.8 2.8	
Rise Time (20 to 80%		2	1.0	2.6	1.0	1.5	2.5	1.0	2.8	
(20 10 00 %	t ₃₊	3	1.0	2.6	1.0	1.5	2.5	1.0	2.8	
Fall Time (20 to 80%	b) t ₂₋	2	1.0	2.6	1.0	1.5	2.5	1.0	2.8	
,	t ₃ _	_	4.0	0.0	4.0	4 5	2.5	1.0	2.8	
OENICE	of Par									

ELECTRICAL CHARACTERISTICS (continued)

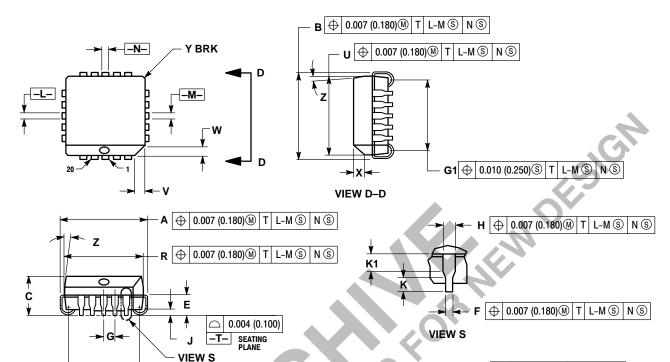
					TES	T VOLTAGI	E VALUES (Volts)		
	(@ Test Tem	perature	V _{IHmax}	V _{ILmin}	V _{IHAmin}	V _{ILAmax}	V _{BB}	V _{EE}	
			-30°C	-0.890	-1.890	-1.205	-1.500	From	-5.2	
		+25°C		-0.810	-1.850	-1.105	-1.475	Pin	-5.2	
			+85°C	-0.700	-1.825	-1.035	-1.440	11	- 5.2	
			Pin	I LOI VOLIAGE ALL LIED TO TIMO LIGITED BELOW					.ow	α, ,
Characteri	Symbol	Under Test	V _{IHmax}	V _{ILmin}	V _{IHAmin}	V _{ILAmax}	V _{BB}	V _{EE}	(V _{CC}) Gnd	
Power Supply Drain C	Current	ΙE	8	4, 9, 12				5, 10, 13	8	1, 16
Input Current		I _{inH}	4	4	9, 12			5, 10, 13	8	1, 16
		Ісво	4 9		9, 12 4, 12			5, 10, 13 5, 10, 13	8, 4 8, 9	1, 16
Output Voltage	Logic 1	V _{OH}	2 3	4 9, 12	9, 12 4			5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Output Voltage	Logic 0	V _{OL}	2 3	9, 12 4	4 9, 12			5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Threshold Voltage	Logic 1	V _{OHA}	2 3	9, 12	9, 12	4	4	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Threshold Voltage	Logic 0	V _{OLA}	2 3	9, 12	9, 12	4	4	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Reference Voltage		V_{BB}	11		\ \ \			5, 10, 13	8	1, 16
Switching Times	(50Ω Load)					Pulse In	Pulse Out		-3.2 V	+2.0 V
Propagation Delay		t ₄₊₂₊ t ₄₋₂₋ t ₄₊₃₋ t ₄₋₃₊	2 2 3 3			4 4 4 4	2 2 3 3	5, 10, 13 5, 10, 13 5, 10, 13 5, 10, 13	8 8 8	1, 16 1, 16 1, 16 1, 16
Rise Time	(20 to 80%)	t ₂₊ t ₃₊	2 3			4 4	2 3	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16
Fall Time	(20 to 80%)	t ₂₋ t ₃₋	2 3			4 4	2 3	5, 10, 13 5, 10, 13	8 8	1, 16 1, 16

Each MECL 10,000 series circuit has been designed to meet the dc specifications shown in the test table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 500 linear fpm is maintained. Outputs are terminated through a 50–ohm resistor to –2.0 volts. Test procedures are shown for only one gate. The other gates are tested in the same manner.

PACKAGE DIMENSIONS

PLCC-20 **FN SUFFIX**

PLASTIC PLCC PACKAGE CASE 775-02 ISSUE C



NOTES:

G1 ⊕ 0.010 (0.250)③ T L-M ⑤ N ⑤

OF MICE. NOT PERSON

- IOTES:

 1. DATUMS -L-, -M-, AND -N- DETERMINED WHERE TOP OF LEAD SHOULDER EXITS PLASTIC BODY AT MOLD PARTING LINE.

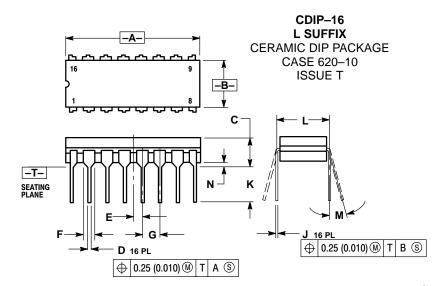
 2. DIMENSION G1, TRUE POSITION TO BE MEASURED AT DATUM -T-, SEATING PLANE.

 3. DIMENSIONS R AND U DO NOT INCLUDE MOLD FLASH. ALLOWABLE MOLD FLASH IS 0.010 (0.250) PER SIDE.

 4. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M. 1982.
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- THE PACKAGE TOP MAY BE SMALLER THAN THE PACKAGE BOTTOM BY UP TO 0.012 (0.300). DIMENSIONS R AND U ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY EXCLUSIVE OF MOLD FLASH, TIE BAR BURRS, GATE BURRS AND INTERLEAD FLASH, BUT INCLUDING ANY MISMATCH BETWEEN THE TOP AND BOTTOM OF THE PLASTIC BODY.
- DIMENSION H DOES NOT INCLUDE DAMBAR PROTRUSION OR INTRUSION. THE DAMBAR PROTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE GREATER THAN 0.037 (0.940). THE DAMBAR INTRUSION(S) SHALL NOT CAUSE THE H DIMENSION TO BE SMALLER THAN 0.025 (0.635).

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.385	0.395	9.78	10.03
В	0.385	0.395	9.78	10.03
С	0.165	0.180	4.20	4.57
Ε	0.090	0.110	2.29	2.79
F	0.013	0.019	0.33	0.48
G	0.050	BSC	1.27	BSC
Н	0.026	0.032	0.66	0.81
J	0.020		0.51	
K	0.025		0.64	
R	0.350	0.356	8.89	9.04
U	0.350	0.356	8.89	9.04
٧	0.042	0.048	1.07	1.21
W	0.042	0.048	1.07	1.21
X	0.042	0.056	1.07	1.42
Υ		0.020		0.50
Z	2°	10°	2°	10 °
G1	0.310	0.330	7.88	8.38
K1	0.040		1.02	

PACKAGE DIMENSIONS



NOTES:

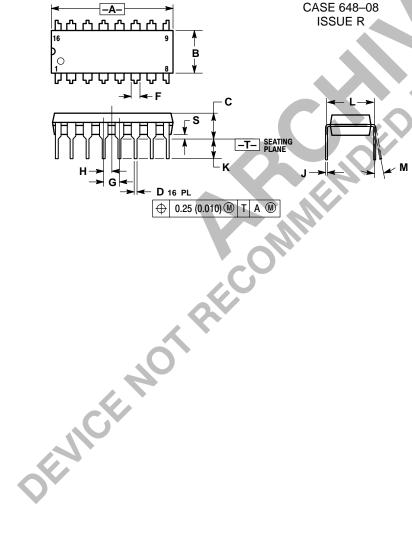
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION LTO CENTER OF LEAD WHEN CONTROLLING DIMENSION LTO CENTER OF LEAD WHEN

- FORMED PARALLEL

 DIMENSION F MAY NARROW TO 0.76 (0.030)
 WHERE THE LEAD ENTERS THE CERAMIC
 BODY.

	INC	HES	MILLIMETERS		
DIM	MIN MAX		MIN	MAX	
Α	0.750	0.785	19.05	19.93	
В	0.240	0.295	6.10	7.49	
С		0.200		5.08	
D	0.015	0.020	0.39	0.50	
Е	0.050	BSC	1.27 BSC		
F	0.055 0.065		1.40	1.65	
G	0.100	BSC	2.54 BSC		
Н	0.008	0.015	0.21	0.38	
K	0.125	0.170	3.18	4.31	
L	0.300	BSC	7.62 BSC		
М	0 °	15°	0 °	15°	
N	0.020	0.040	0.51	1.01	

PDIP-16 **P SUFFIX** PLASTIC DIP PACKAGE CASE 648-08 ISSUE R



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL

	INC	HES	MILLIN	IETERS	
DIM	MIN	MIN MAX		MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100	BSC	2.54	BSC	
Н	0.050	BSC	1.27	BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10°	0°	10 °	
S	0.020	0.040	0.51	1.01	

Notes



Notes





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